A5G07H800W19N

Airfast RF Power GaN Transistor

Rev. 2 — 30 May 2025 Product data sheet

1 General description

This 112 W asymmetrical Doherty RF power GaN transistor is designed for cellular base station applications requiring very wide instantaneous bandwidth capability covering the frequency range of 717 MHz to 850 MHz.

This part is characterized and performance is guaranteed for applications operating in the 717 MHz to 850 MHz band. There is no guarantee of performance when this part is used in applications designed outside of these frequencies.

2 Features and benefits

- High terminal impedances for optimal broadband performance
- Advanced high performance in-package Doherty
- Improved linearized error vector magnitude with next generation signal
- Able to withstand extremely high output VSWR and broadband operating conditions
- Plastic package

3 Typical performance

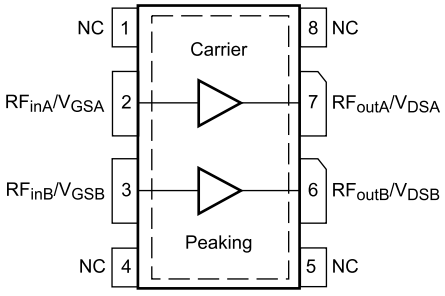
Table 1. 800 MHz — Typical Doherty single-carrier W-CDMA reference circuit performance

V_{DD} = 48 Vdc, I_{DQA} = 300 mA, V_{GSB} = –5.0 Vdc, P_{out} = 112 W Avg., Input Signal PAR = 9.9 dB @ 0.01% Probability on CCDF.[1]

Frequency	G_{ps} (dB)	η_D (%)	Output PAR (dB)	ACPR (dBc)
758 MHz	19.7	61.2	8.9	–26.5
803 MHz	19.3	60.0	9.1	–29.3
821 MHz	18.8	59.8	9.0	–30.0

[1] All data measured with device soldered to NXP reference circuit.

4 Pinning information



(Top view)

Note: Exposed backside of the package is the source terminal for the transistor.

Figure 1. Pin configuration

5 Ordering information

Table 2. Ordering information

Device	Tape and Reel Information	Package
A5G07H800W19NR3	R3 Suffix = 250 Units, 44 mm Tape Width, 13-inch Reel	OM-780-4S4S

6 Product marking

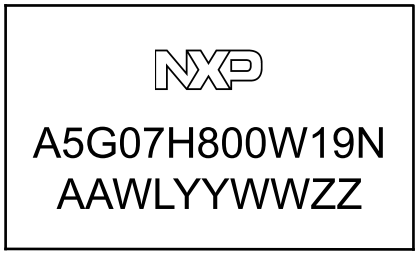


Figure 2. Product marking

Table 3. Product marking trace code

Identifier	Description
AA	Assembly location
WL	Wafer lot indicator
YYWW	Date code
ZZ	Assembly lot

7 Limiting values

Table 4. Limiting values

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	125	Vdc
Gate-Source Voltage	V_{GS}	–16, 0	Vdc
Operating Voltage	V_{DD}	55	Vdc
Maximum Forward Gate Current, $I_{G\ (A+B)}$, @ T_C = 25°C	I_{GMAX}	90	mA
Storage Temperature Range	T_{stg}	–65 to +150	°C
Case Operating Temperature Range	T_C	–55 to +150	°C
Maximum Channel Temperature	T_{CH}	225	°C

8 Recommended operating conditions

Table 5. Recommended operating conditions

Characteristic	Symbol	Value	Unit
Operating Voltage	V_{DD}	50	Vdc

9 Thermal characteristics

Table 6. Thermal characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance by Infrared Measurement, Active Die Surface-to-Case Case Temperature 88°C, P_D = 95 W	$R_{\theta SC}$ (IR)	0.43[1]	°C/W
Thermal Resistance by Finite Element Analysis, Channel-to-Case Case Temperature 88°C, P_D = 94.7 W	$R_{\theta CHC}$ (FEA)	0.6[2]	°C/W

[1] Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to https://www.nxp.com/RF and search for AN1955.

[2] $R_{\theta CHC}$ (FEA) must be used for purposes related to reliability and limitations on maximum channel temperature. MTTF may be estimated by the expression MTTF (hours) = $10^{[A+B/(T+273)]}$, where T is the channel temperature in degrees Celsius, A = –11.6 and B = 9129.

10 ESD protection characteristics

Table 7. ESD protection characteristics

Test Methodology	Class
Human Body Model (per JS-001-2017)	1A
Charge Device Model (per JS-002-2014)	C3

11 Moisture sensitivity level

Table 8. Moisture sensitivity level

Test Methodology	Rating	Package Peak Temperature	Unit
Per JESD22-A113, IPC/JEDEC J-STD-020	3	245	°C

12 Electrical characteristics

12.1 DC characteristics — off characteristics

Table 9. DC characteristics — off characteristics

(T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Off characteristics[1]					
Off-State Drain Leakage (V_{DS} = 150 Vdc, V_{GS} = –8 Vdc) Carrier (V_{DS} = 150 Vdc, V_{GS} = –8 Vdc) Peaking	$I_{D(BR)}$	 — —	 — —	 15.4 26.4	mAdc

[1] Each side of device measured separately.

12.2 DC characteristics — on characteristics

Table 10. DC characteristics — on characteristics

(T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
On characteristics — Side A, Carrier					
Gate Threshold Voltage (V_{DS} = 10 Vdc, I_D = 35 mAdc)	$V_{GS(th)}$	–4.6	–2.6	–1.9	Vdc
Gate Quiescent Voltage (V_{DD} = 50 Vdc, I_D = 350 mAdc, Measured in Functional Test)	$V_{GSA(Q)}$	–3.1	–2.6	–2.1	Vdc
On characteristics — Side B, Peaking					
Gate Threshold Voltage (V_{DS} = 10 Vdc, I_D = 60 mAdc)	$V_{GS(th)}$	–4.6	–2.6	–1.9	Vdc

12.3 Functional tests

Table 11. Functional tests

(In NXP Doherty Production Test Fixture, T_A = 25°C unless otherwise noted, 50 ohm system)[1] *V_{DD} = 50 Vdc, I_{DQA} = 350 mA, V_{GSB} = (V_t – 2.4) Vdc, P_{out} = 158 W Avg., f = 758 MHz, Single-Carrier W-CDMA, IQ Magnitude Clipping, Input Signal PAR = 9.9 dB @ 0.01% Probability on CCDF. ACPR measured in 3.84 MHz Channel Bandwidth @ ±5 MHz Offset.*

Characteristic	Symbol	Min	Typ	Max	Unit
Power Gain	G_{ps}	17.4	18.3	19.7	dB
Drain Efficiency	η_D	57.0	60.8	—	%
Saturated Power (Pulsed CW, 5% Duty Cycle)	P_{sat}	58.0	59.9	—	dBm
Adjacent Channel Power Ratio	ACPR	—	–32.8	–29.0	dBc

[1] Internally matched part.

12.4 Wideband ruggedness

Table 12. Wideband ruggedness

(In NXP Doherty Production Test Fixture, T_A = 25°C unless otherwise noted, 50 ohm system) I_{DQA} = 350 mA, V_{GSB} = –5.0 Vdc, f = 790 MHz, Additive White Gaussian Noise (AWGN) with 10 dB PAR.

Characteristic	Symbol	Min	Typ	Max	Unit
ISBW of 400 MHz at 55 Vdc, 174 W Avg. Modulated Output Power (3 dB Input Overdrive from 100 W Avg. Modulated Output Power)	No Device Degradation				

12.5 Typical performance

Table 13. Typical performance

(In NXP Doherty Production Test Fixture, T_A = 25°C unless otherwise noted, 50 ohm system) V_{DD} = 50 Vdc, I_{DQA} = 350 mA, V_{GSB} = –4.8 Vdc, 758–821 MHz Bandwidth.

Characteristic	Symbol	Min	Typ	Max	Unit
Pulsed CW, 10% duty cycle					
Saturated Power[1]	P_{sat}	—	955	—	W
AM/PM[1] (Maximum value measured at saturated power across the 758–821 MHz bandwidth)	Φ	—	–30	—	°
Gain Variation @ Avg. Power over Temperature (–40°C to +85°C)	ΔG	—	0.005	—	dB/°C
Output Power Variation @ Saturated Power over Temperature (–40°C to +85°C)	ΔP_{sat}	—	0.001	—	dB/°C
Single-carrier W-CDMA, unclipped					
Gain Flatness in 63 MHz Bandwidth @ P_{out} = 112 W Avg.[1]	G_F	—	0.9	—	dB
2-tone CW					
VBW Resonance Point[1] (IMD Third Order Intermodulation Inflection Point)	VBW_{res}	—	70	—	MHz

[1] All data measured with device soldered to NXP production test fixture.

Correct biasing sequence for GaN depletion mode transistors in a Doherty configuration

Bias ON the device

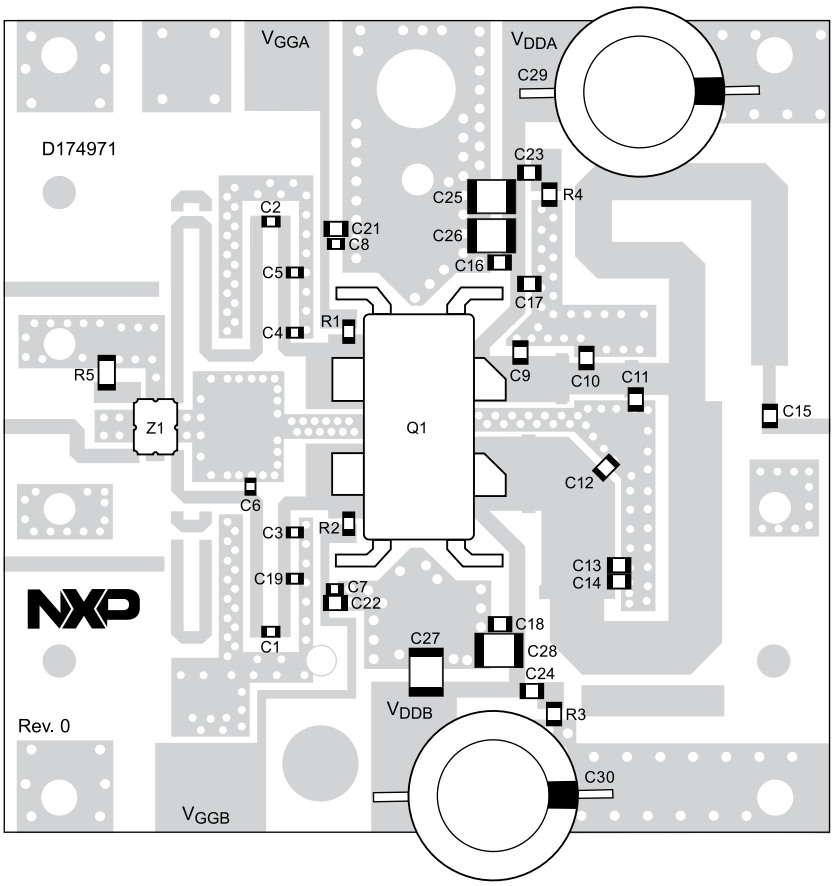
1. Set gate voltage V_{GSA} and V_{GSB} to –5 V.
2. Set drain voltage V_{DSA} and V_{DSB} to nominal supply voltage (+50 V).
3. Increase V_{GSA} (carrier side) until I_{DQA} current is attained.
4. Increase V_{GSB} (peaking side) to target bias voltage.
5. Apply RF input power to desired level.

Bias OFF the device

1. Disable RF input power.
2. Adjust gate voltage V_{GSA} and V_{GSB} to –5 V.
3. Adjust drain voltage V_{DSA} and V_{DSB} to 0 V. Allow adequate time for drain voltage to reduce to 0 V from external drain capacitors.
4. Disable V_{GSA} and V_{GSB}.

13 Component layout and parts list

13.1 Component layout



Note: All data measured with device soldered to NXP reference circuit.

aaa-051061

Figure 3. A5G07H800W19N reference circuit component layout — 2.95″ (7.5 cm) × 3.0″ (7.6 cm)

13.2 Component designations and values

Table 14. A5G07H800W19N reference circuit component designations and values

Part	Description	Part Number	Manufacturer
C1, C2, C7, C8	100 pF Chip Capacitor	600S101JT250XT	ATC
C3	12 pF Chip Capacitor	GQM1875C2E120FB12D	Murata
C4	9.1 pF Chip Capacitor	GQM1875C2E9R1BB12D	Murata
C5	6.8 pF Chip Capacitor	GQM1875C2E6R8BB12D	Murata
C6	1.2 pF Chip Capacitor	GQM1875C2E1R2BB12D	Murata
C9	2.2 pF Chip Capacitor	600F2R2BT250XT	ATC
C10	6.8 pF Chip Capacitor	600F6R8BT250XT	ATC
C11	12 pF Chip Capacitor	600F120JT250XT	ATC
C12	15 pF Chip Capacitor	600F150JT250XT	ATC
C13	9.1 pF Chip Capacitor	600F9R1BT250XT	ATC
C14	5.1 pF Chip Capacitor	600F5R1BT250XT	ATC
C15, C16, C17, C18	100 pF Chip Capacitor	600F101JT250XT	ATC
C19	4.3 pF Chip Capacitor	GQM1875C2E4R3BB12D	Murata
C21, C22	4.7 µF Chip Capacitor	GQM2195C2E4R7BB12D	Murata
C23, C24	10 nF Chip Capacitor	GRM21BR72A103KA01B	Murata
C25, C26, C27, C28	4.7 µF Chip Capacitor	C4532X7S2A475M	TDK
C29, C30	470 µF, 100 V Electrolytic Capacitor	MCGPR100V477M16X32	Multicomp
Q1	RF Power GaN Transistor	A5G07H800W19N	NXP
R1, R2	3.0 Ω, 1/8 W Chip Resistor	CRCW08053R00JNEA	Vishay
R3, R4	10 Ω, 1/8 W Chip Resistor	CRCW080510R0FKEA	Vishay
R5	50 Ω, 8 W Termination Chip Resistor	C8A50Z4B	Anaren
Z1	800–1000 MHz Band, 90°, 2 dB Asymmetric Coupler	CMX09Q02	RN2 Technologies
PCB	Rogers, RO4350B, 0.020″, ε_r = 3.66	D174971	MTL

Note: Component number C20 is intentionally omitted.

14 Package information

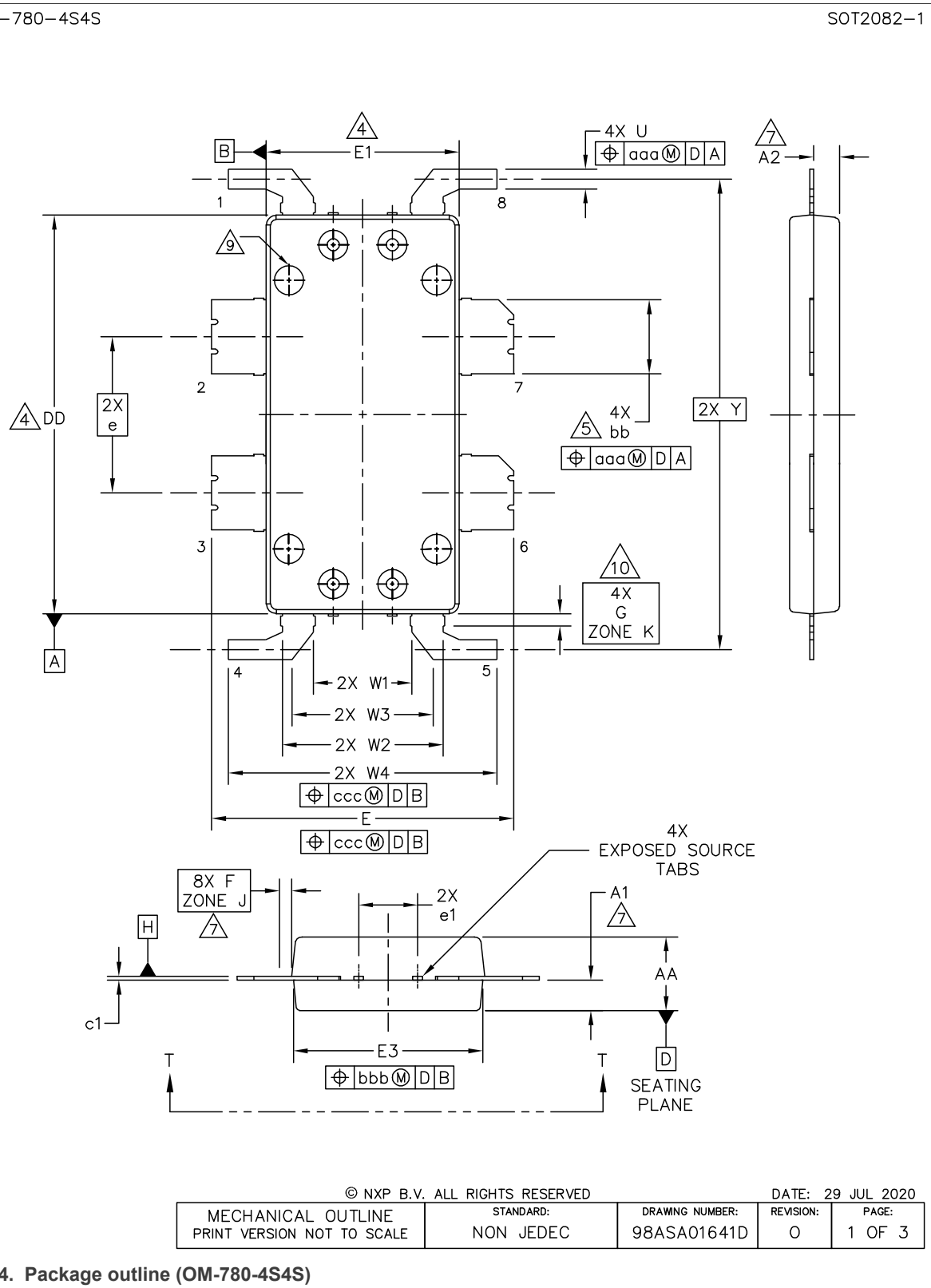
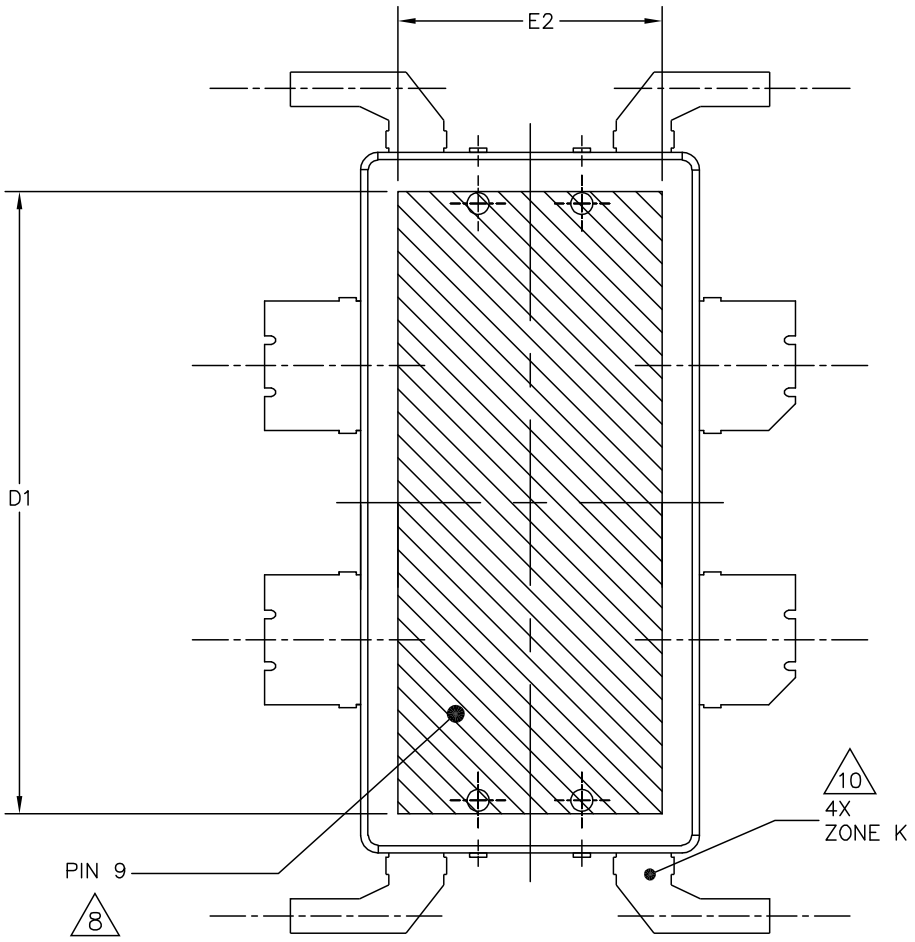


Figure 4. Package outline (OM-780-4S4S)

OM−780−4S4S SOT2082−1



BOTTOM VIEW
VIEW T−T

DATE: 29 JUL 2020

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Figure 5. Package outline (OM-780-4S4S) — bottom view

OM−780−4S4S SOT2082−1

NOTES:
1. CONTROLLING DIMENSION: INCH

2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M−1994.

3. DATUM PLANE H IS LOCATED AT TOP OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE TOP OF THE PARTING LINE.

4. DIMENSIONS DD AND E1 DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS .006 INCH (0.15 MM) PER SIDE. DIMENSIONS DD AND E1 DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE H.

5. DIMENSION bb DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE .005 INCH (0.13 MM) TOTAL IN EXCESS OF THE bb DIMENSION AT MAXIMUM MATERIAL CONDITION.

6. DATUMS A AND B TO BE DETERMINED AT DATUM PLANE H.

7. DIMENSIONS A1 AND A2 APPLIES WITHIN ZONE J ONLY. A1 APPLIES TO PINS 2, 3, 6 AND 7. A2 APPLIES TO PINS 1, 4, 5 AND 8.

8. HATCHING REPRESENTS THE EXPOSED AREA OF THE HEAT SLUG. THE DIMENSIONS D1 AND E2 REPRESENT THE VALUES BETWEEN THE TWO OPPOSITE POINTS ALONG THE EDGES OF EXPOSED AREA OF HEAT SLUG.

9. DIMPLED HOLE REPRESENTS INPUT SIDE.

10. ZONE K REPRESENTS NON−SOLDERABLE REGION WHERE MOLD FLASH AND RESIN BLEED ARE PERMITTED ON BOTH SIDES OF THE LEADS.

DIM	INCH		MILLIMETER		DIM	INCH		MILLIMETER	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
AA	.148	.152	3.76	3.86	W2	.321	.331	8.15	8.41
A1	.059	.065	1.50	1.65	W3	.281	.291	7.14	7.39
A2	.056	.068	1.42	1.73	W4	.538	.554	13.67	14.07
DD	.808	.812	20.52	20.62	U	.037	.043	0.94	1.09
D1	.720	----	18.29	----	Y	.956 BSC		24.28 BSC	
E	.610	.618	15.49	15.70	bb	.147	.153	3.73	3.89
E1	.390	.394	9.91	10.01	c1	.007	.011	0.18	0.28
E2	.306	----	7.77	----	e	.317 BSC		8.05 BSC	
E3	.383	.387	9.73	9.83	e1	.116	.124	2.95	3.15
F	.025 BSC		0.64 BSC		aaa	.004		0.10	
G	.030 BSC		0.76 BSC		bbb	.006		0.15	
W1	.195	.205	4.95	5.21	ccc	.010		0.25	

DATE: 29 JUL 2020

MECHANICAL OUTLINE PRINT VERSION NOT TO SCALE	STANDARD: NON JEDEC	DRAWING NUMBER: 98ASA01641D	REVISION: O	PAGE: 3

Figure 6. Package outline (OM-780-4S4S) — notes, dimensions

15 Product documentation, software and tools

Refer to the following resources to aid your design process.

Application notes

- AN1907: Solder Reflow Attach Method for High Power RF Devices in Plastic Packages
- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

Software

- .s2p File

Development tools

- Printed Circuit Boards

16 Revision history

The following table summarizes revisions to this document.

Table 15. Revision history

Document ID	Release date	Description
A5G07H800W19N v.2	30 May 2025	• Fig. 2, Product marking: updated, p. 2 • Table 3, Product marking trace code: updated, p. 2
A5G07H800W19N v.1	21 December 2023	• Table 8, Moisture Sensitivity Level: package peak temperature updated to reflect actual test data, p. 3 • Table 10, DC On Characteristics, $V_{GSA(Q)}$: updated Min value to match production test value, p. 4 • Table 11, Functional Tests: updated output power test condition, p. 4 • Table 13, Typical Performance: added VBW_{res}, p. 5 • General updates made to align data sheet to current standard
A5G07H800W19N v.0	12 April 2023	• Initial release of data sheet

Legal information

Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
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